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With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

Darlington Amplifier Transistors

NPN Silicon

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V_{CES}	30	Vdc
Collector – Base Voltage	V_{CBO}	30	Vdc
Emitter – Base Voltage	V_{EBO}	10	Vdc
Collector Current – Continuous	I_C	300	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

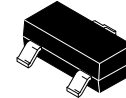
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

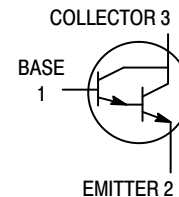


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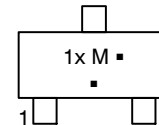
www.onsemi.com



SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



- 1x = Device Code
 x = M for MMBTA13LT1G,
 SMMBTA13LT1G
 x = N for MMBTA14LT1G,
 SMMBTA14LT1G, T3G
 M = Date Code*
 ■ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBTA13LT1G, SMMBTA13LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA14LT1G, SMMBTA14LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA14LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage ($I_C = 100 \mu\text{Adc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	30	–	Vdc
Collector Cutoff Current ($V_{CB} = 30 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	100	nAdc
Emitter Cutoff Current ($V_{EB} = 10 \text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	100	nAdc

ON CHARACTERISTICS (Note 3)

DC Current Gain ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) MMBTA13, SMMBTA13 MMBTA14, SMMBTA14 ($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) MMBTA13, SMMBTA13 MMBTA14, SMMBTA14	h_{FE}	5000 10,000 10,000 20,000	– – – –	–
Collector – Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}$, $I_B = 0.1 \text{ mAdc}$)	$V_{CE(sat)}$	–	1.5	Vdc
Base – Emitter On Voltage ($I_C = 100 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	V_{BE}	–	2.0	Vdc

SMALL – SIGNAL CHARACTERISTICS

Current – Gain – Bandwidth Product (Note 4) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	125	–	MHz
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Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. $f_T = |h_{fe}| \cdot f_{test}$.

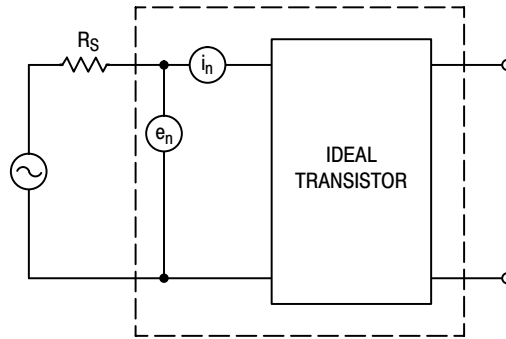


Figure 1. Transistor Noise Model

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

NOISE CHARACTERISTICS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$)

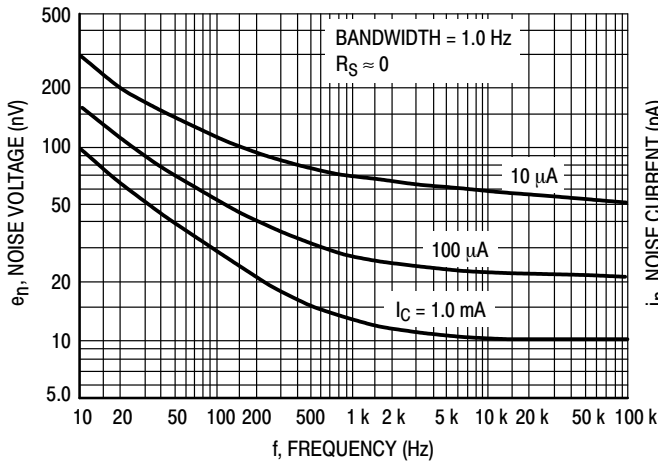


Figure 2. Noise Voltage

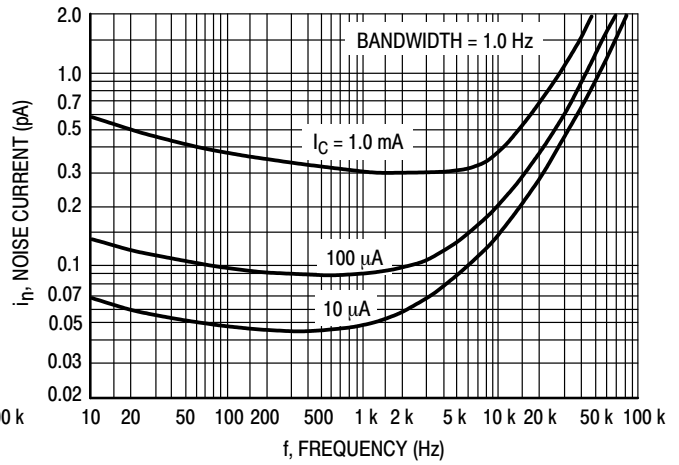


Figure 3. Noise Current

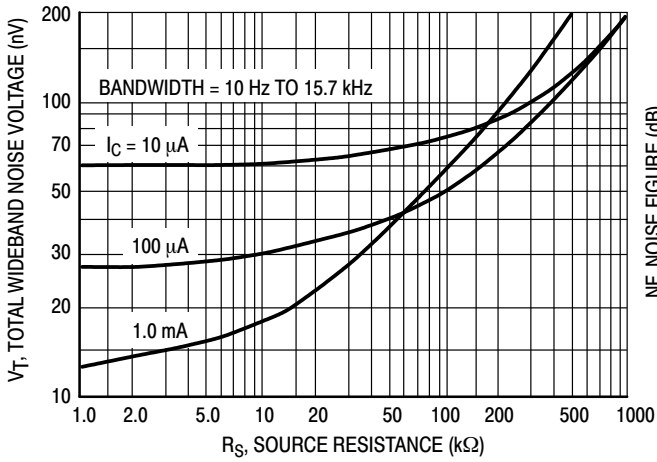


Figure 4. Total Wideband Noise Voltage

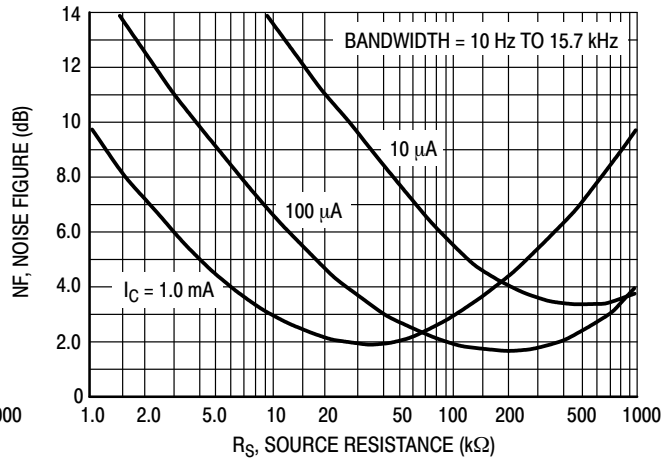


Figure 5. Wideband Noise Figure

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

SMALL-SIGNAL CHARACTERISTICS

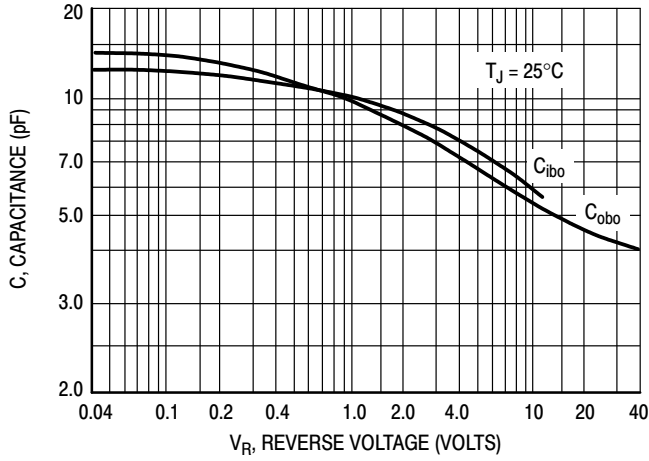


Figure 6. Capacitance

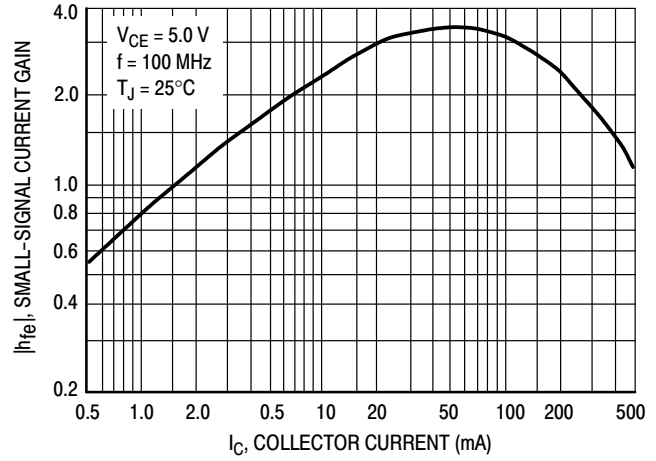


Figure 7. High Frequency Current Gain

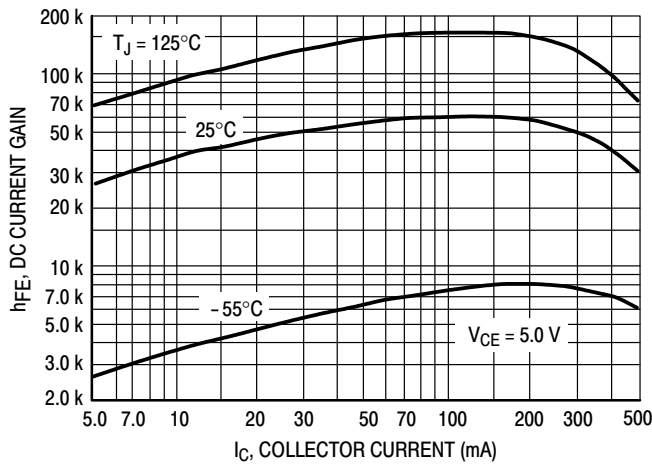


Figure 8. DC Current Gain

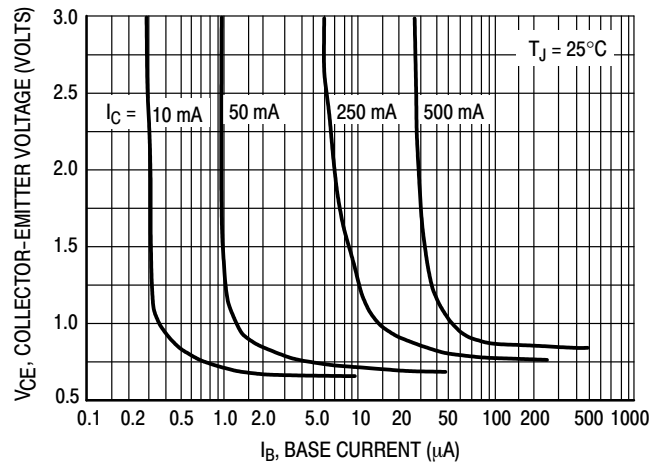


Figure 9. Collector Saturation Region

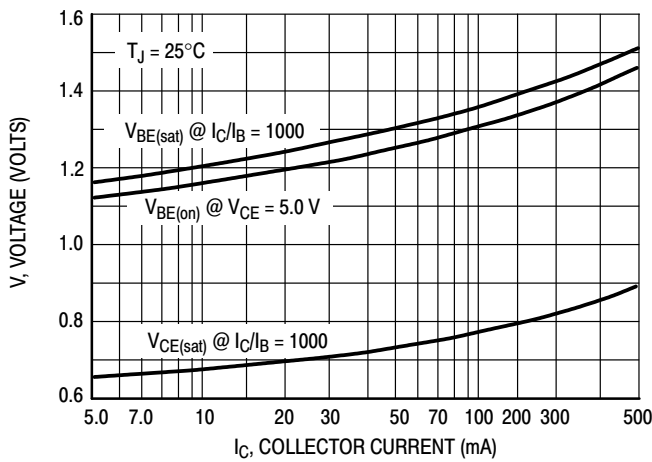


Figure 10. "On" Voltages

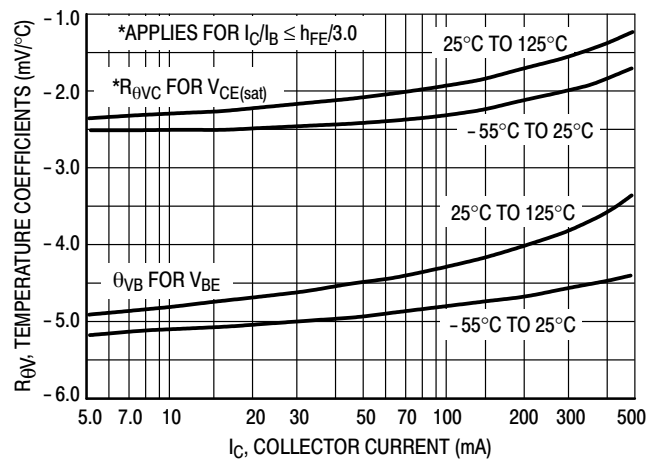


Figure 11. Temperature Coefficients

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

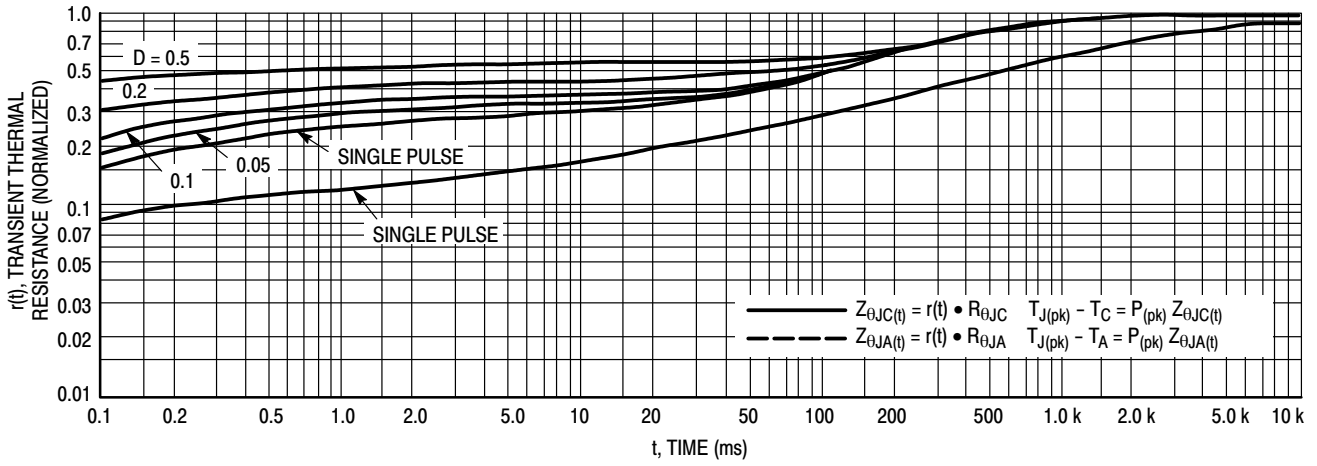


Figure 12. Thermal Response

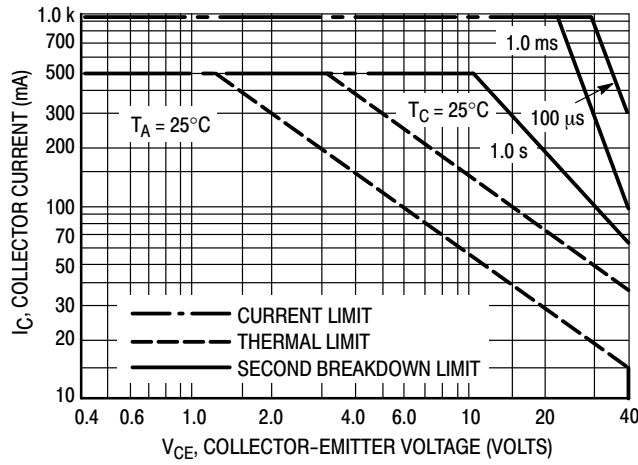
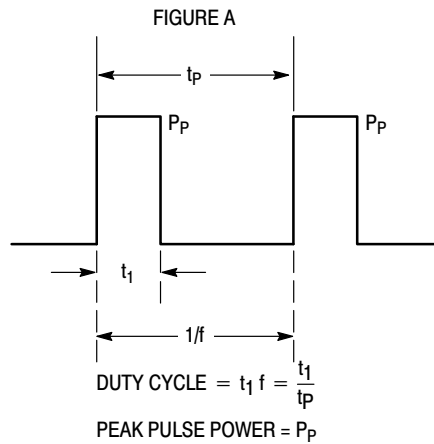


Figure 13. Active Region Safe Operating Area

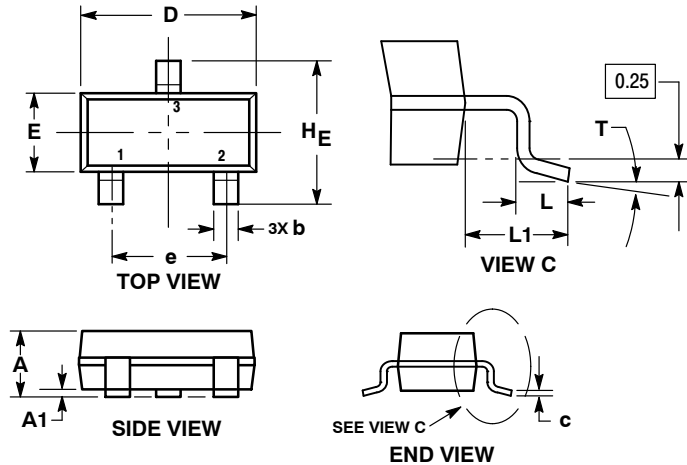


Design Note: Use of Transient Thermal Resistance Data

MMBTA13L, SMMBTA13L, MMBTA14L, SMMBTA14L

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AR

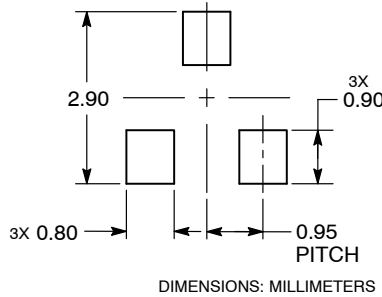


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

- STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

RECOMMENDED SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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